## LME49870

LME49870 44V Single High Performance, High Fidelity Audio Operational Amplifier



Literature Number: SNAS413B

www.BDTIC.com/TI



## LME49870

# 44V Single High Performance, High Fidelity Audio Operational Amplifier

### **General Description**

The LME49870 is part of the ultra-low distortion, low noise, high slew rate operational amplifier series optimized and fully specified for high performance, high fidelity applications. Combining advanced leading-edge process technology with state-of-the-art circuit design, the LME49870 audio operational amplifier delivers superior audio signal amplification for outstanding audio performance. The LME49870 combines extremely low voltage noise density  $(2.7\text{nV}/\sqrt{\text{Hz}})$  with vanishingly low THD+N (0.00003%) to easily satisfy the most demanding audio applications. To ensure that the most challenging loads are driven without compromise, the LME49870 has a high slew rate of  $\pm 20\text{V}/\mu\text{s}$  and an output current capability of  $\pm 26\text{mA}$ . Further, dynamic range is maximized by an output stage that drives  $2k\Omega$  loads to within 1V of either power supply voltage and to within 1.4V when driving  $600\Omega$  loads.

The LME49870's outstanding CMRR (120dB), PSRR (120dB), and  $\rm V_{OS}$  (0.1mV) give the amplifier excellent operational amplifier DC performance.

The LME49870 has a wide supply range of ±2.5V to ±22V. Over this supply range the LME49870 maintains excellent common-mode rejection, power supply rejection, and low input bias current. The LME49870 is unity gain stable. This Audio Operational Amplifier achieves outstanding AC performance while driving complex loads with values as high as 100pF.

The LME49870 is available in 8-lead narrow body SOIC. Demonstration boards are available for each package.

### **Key Specifications**

■ Power Supply Voltage Range

±2.5V to ±22V

■ THD+N

 $(A_V = 1, V_{OUT} = 3V_{RMS}, f_{IN} = 1kHz)$ 

$R_L = 2k\Omega$	0.00003% (typ)
$R_L = 600\Omega$	0.00003% (typ)
■ Input Noise Density	$2.7 \text{nV}/\sqrt{\text{Hz}}$ (typ)
■ Slew Rate	±20V/µs (typ)
■ Gain Bandwidth Product	55MHz (typ)
■ Open Loop Gain (R <sub>L</sub> = 600Ω)	140dB (typ)
■ Input Bias Current	10nA (typ)
■ Input Offset Voltage	0.1mV (typ)
■ DC Gain Linearity Error	0.000009%

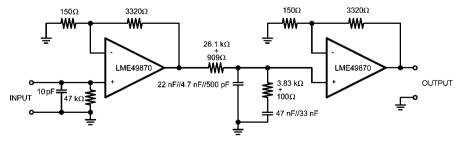
### **Features**

- Easily drives 600Ω loads
- Optimized for superior audio signal fidelity
- Output short circuit protection
- PSRR and CMRR exceed 120dB (typ)

### **Applications**

- High quality audio amplification
- High fidelity preamplifiers, phono preamps, and multimedia
- High performance professional audio
- High fidelity equalization and crossover networks with active filters
- High performance line drivers and receivers
- Low noise industrial applications including test, measurement, and ultrasound

## **Typical Application**

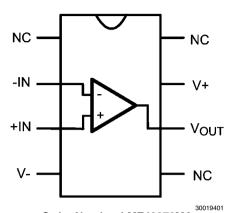


Note: 1% metal film resistors, 5% polypropylene capacitors

**Passively Equalized RIAA Phono Preamplifier** 

300194k5

### **Connection Diagrams**



Order Number LME49870MA
See NS Package Number — M08A

LME49870 Top Mark

NZXTT L49870 MA

30019402

N — National Logo
Z — Assembly Plant code
X — 1 Digit Date code
TT — Die Traceability
L49870 — LME49870
MA — Package code

145°C/W

### **Absolute Maximum Ratings** (Notes 1, 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Power Supply Voltage

 $(V_S = V^+ - V^-)$  46V Storage Temperature  $-65^{\circ}$ C to 150°C Input Voltage  $(V^-) - 0.7V$  to  $(V^+) + 0.7V$ 

Output Short Circuit (Note 3) Continuous

Power Dissipation Internally Limited ESD Rating (Note 4) 2000V

ESD Rating (Note 5)

Pins 1, 4, 7 and 8 200V Pins 2, 3, 5 and 6 100V Junction Temperature 150°C Thermal Resistance

### **Operating Ratings**

Temperature Range

 $\theta_{JA}$  (SO)

 $T_{MIN} \le T_A \le T_{MAX}$   $-40^{\circ}C \le T_A \le 85^{\circ}C$ Supply Voltage Range  $\pm 2.5V \le V_S \le \pm 22V$ 

**Electrical Characteristics for the LME49870** (Note 1) The following specifications apply for  $V_S = \pm 18V$  and  $\pm 22V$ ,  $R_L = 2k\Omega$ ,  $R_{SOURCE} = 10\Omega$ ,  $f_{IN} = 1kHz$ ,  $T_A = 25^{\circ}C$ , unless otherwise specified.

			LME49870		
Symbol	Parameter	Conditions	Typical	Limit	Units
			(Note 6)	(Note 7)	(Limits)
THD+N	Total Harmonic Distortion + Noise	$A_{V} = 1, V_{OUT} = 3V_{rms}$ $R_{L} = 2k\Omega$ $R_{L} = 600\Omega$	0.00003 0.00003	0.00009	% (max)
IMD	Intermodulation Distortion	$A_V = 1$ , $V_{OUT} = 3V_{RMS}$ Two-tone, 60Hz & 7kHz 4:1	0.00005		%
GBWP	Gain Bandwidth Product		55	45	MHz (min)
SR	Slew Rate		±20	±15	V/µs (min)
FPBW	Full Power Bandwidth	V <sub>OUT</sub> = 1V <sub>P-P</sub> , -3dB referenced to output magnitude at f = 1kHz	10		MHz
t <sub>s</sub>	Settling time	$A_V = -1$ , 10V step, $C_L = 100pF$ 0.1% error range	1.2		μs
	Equivalent Input Noise Voltage	f <sub>BW</sub> = 20Hz to 20kHz	0.34	0.65	μV <sub>RMS</sub> (max)
e <sub>n</sub>	Equivalent Input Noise Density	f = 1kHz f = 10Hz	2.5 6.4	4.7	nV/√ <del>Hz</del> (max)
i <sub>n</sub>	Current Noise Density	f = 1kHz f = 10Hz	1.6 3.1		pA∕√Hz
V <sub>OS</sub>	Offset Voltage	V <sub>S</sub> = ±18V	±0.12		mV (max)
		V <sub>S</sub> = ±22V	±0.14	±0.7	mV (max)
$\Delta V_{OS}/\Delta Temp$	Average Input Offset Voltage Drift vs Temperature	-40°C ≤ T <sub>A</sub> ≤ 85°C	0.1		μV/°C
PSRR	Average Input Offset Voltage Shift vs Power Supply Voltage	$V_S = \pm 18V, \ \Delta V_S = 24V \ (Note 8)$ $V_S = \pm 22V, \ \Delta V_S = 30V$	120 120	110	dB (min)
I <sub>B</sub>	Input Bias Current	$V_{CM} = 0V$	10	72	nA (max)
ΔI <sub>OS</sub> /ΔTemp	Input Bias Current Drift vs Temperature	-40°C ≤ T <sub>A</sub> ≤ 85°C	0.2		nA/°C
I <sub>os</sub>	Input Offset Current	V <sub>CM</sub> = 0V	11	65	nA (max)
	Common-Mode Input Voltage Range	V <sub>S</sub> = ±18V	+17.1 -16.9		V (min) V (min)
V <sub>IN-CM</sub>		V <sub>S</sub> = ±22V	+21.0 -20.8	(V+) - 2.0 (V-) + 2.0	V (min) V (min)

Symbol	Parameter		LME4	LME49870	
		Conditions	Typical	Typical Limit	
			(Note 6)	(Note 7)	(Limits)
		V <sub>S</sub> = ±18V	100		ID (
	Common Mada Baiastian	–12V≤Vcm≤12V	120		dB (min)
CMRR	Common-Mode Rejection	V <sub>S</sub> = ±22V	100	110	1
	1	–15V≤Vcm≤15V	120	110	dB (min)
7	Differential Input Impedance		30		kΩ
Z <sub>IN</sub>	Common Mode Input Impedance	-10V <vcm<10v< td=""><td>1000</td><td></td><td>MΩ</td></vcm<10v<>	1000		MΩ
		V <sub>S</sub> = ±18V			
		–12V≤Vout≤12V			
		$R_L = 600\Omega$	140		dB
		$R_L = 2k\Omega$	140		dB
٨	Onen Leen Veltege Cein	$R_L = 10\Omega$	140		dB
$A_{VOL}$	Open Loop Voltage Gain	V <sub>S</sub> = ±22V			
		–15V≤Vout≤15V			
		$R_L = 600\Omega$	140	125	dB
		$R_L = 2k\Omega$	140		dB
		$R_L = 10\Omega$	140		dB
		$R_L = 600\Omega$			
		$V_S = \pm 18V$	±16.7		V (min)
		$V_S = \pm 22V$	±20.4	±19.0	V (min)
		$R_L = 2k\Omega$			
$V_{OUTMAX}$	Maximum Output Voltage Swing	$V_S = \pm 18V$	±17.0		V (min)
		V <sub>S</sub> = ±22V	±21.0		V (min)
		$R_L = 10k\Omega$			
		$V_S = \pm 18V$	±17.1		V (min)
		V <sub>S</sub> = ±22V	±21.0		V (min)
	Output Current	$R_L = 600\Omega$			
I <sub>OUT</sub>		$V_S = \pm 20V$	±31		mA (mir
		V <sub>S</sub> = ±22V	±37	±30	mA (mir
оит-сс	Instantaneous Short Circuit Current		+53 -42		mA
R <sub>OUT</sub>	Output Impedance	f <sub>IN</sub> = 10kHz	-42		
		Closed-Loop	0.01		Ω
		Open-Loop	13		
C <sub>LOAD</sub>	Capacitive Load Drive Overshoot	100pF	16		%
I <sub>S</sub>	Total Quiescent Current	I <sub>OUT</sub> = 0mA	5	6.5	mA (max

**Note 1:** "Absolute Maximum Ratings" indicate limits beyond which damage to the device may occur, including inoperability and degradation of device reliability and/or performance. Functional operation of the device and/or non-degradation at the Absolute Maximum Ratings or other conditions beyond those indicated in the Recommended Operating Conditions is not implied. The Recommended Operating Conditions indicate conditions at which the device is functional and the device should not be operated beyond such conditions. All voltages are measured with respect to the ground pin, unless otherwise specified.

Note 2: The Electrical Characteristics tables list guaranteed specifications under the listed Recommended Operating Conditions except as otherwise modified or specified by the Electrical Characteristics Conditions and/or Notes. Typical specifications are estimations only and are not guaranteed.

Note 3: The maximum power dissipation must be derated at elevated temperatures and is dictated by  $T_{JMAX}$ ,  $\theta_{JA}$ , and the ambient temperature,  $T_A$ . The maximum allowable power dissipation is  $P_{DMAX} = (T_{JMAX} - T_A) / \theta_{JA}$  or the number given in *Absolute Maximum Ratings*, whichever is lower.

Note 4: Human body model, applicable std. JESD22-A114C.

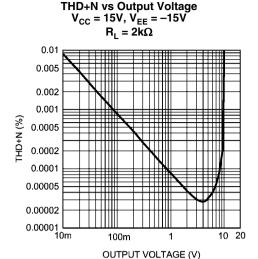
Note 5: Machine model, applicable std. JESD22-A115-A.

Note 6: Typical values represent most likely parametric norms at  $T_A = +25$ °C, and at the *Recommended Operation Conditions* at the time of product characterization and are not guaranteed.

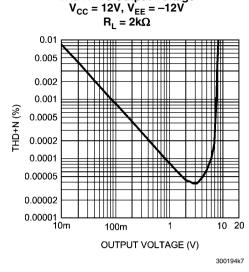
 $\textbf{Note 7:} \ \ \textbf{Datasheet min/max specification limits are guaranteed by test or statistical analysis.}$ 

Note 8: PSRR is measured as follows: For  $V_S$ ,  $V_{OS}$  is measured at two supply voltages,  $\pm 7V$  and  $\pm 22V$ , PSRR =  $|20\log(\Delta V_{OS}/\Delta V_S)|$ .

### **Typical Performance Characteristics**

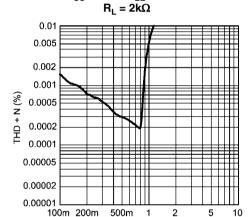


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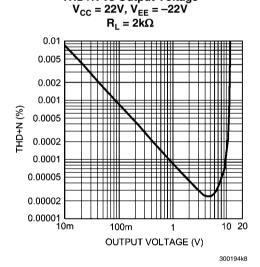


THD+N vs Output Voltage

THD+N vs Output Voltage  $V_{CC} = 2.5V$ ,  $V_{EE} = -2.5V$ 

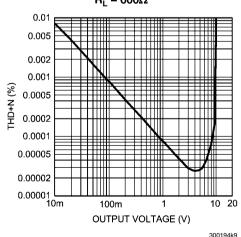


OUTPUT VOLTAGE (V)

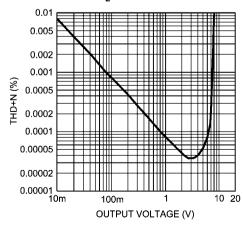


THD+N vs Output Voltage

THD+N vs Output Voltage  $V_{CC} = 15V, \, V_{EE} = -15V \\ R_L = 600\Omega$ 



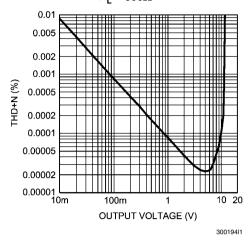
THD+N vs Output Voltage  $V_{CC}$  = 12V,  $V_{EE}$  = -12V  $R_L$  = 600 $\Omega$ 



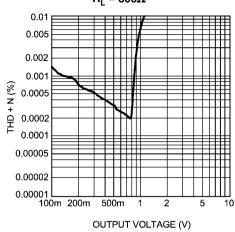
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# THD+N vs Output Voltage $V_{CC}$ = 22V, $V_{EE}$ = -22V $R_{L}$ = 600 $\Omega$

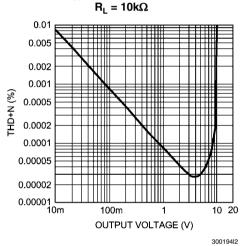


# THD+N vs Output Voltage $V_{CC}$ = 2.5V, $V_{EE}$ = -2.5V $R_{L}$ = 600 $\Omega$

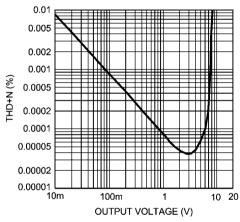


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### THD+N vs Output Voltage $V_{CC} = 15V$ , $V_{EE} = -15V$

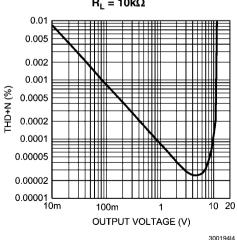


THD+N vs Output Voltage  $V_{CC} = 12V, \, V_{EE} = -12V$   $R_L = 10k\Omega$ 

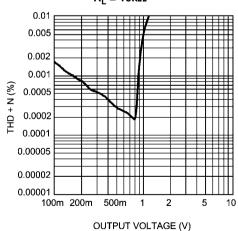


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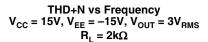
# THD+N vs Output Voltage $V_{CC} = 22V, V_{EE} = -22V$ $R_1 = 10k\Omega$

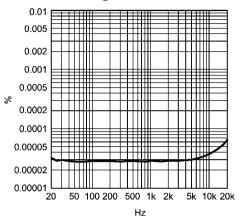


THD+N vs Output Voltage  $V_{CC}$  = 2.5V,  $V_{EE}$  = -2.5V  $R_{I}$  = 10k $\Omega$ 



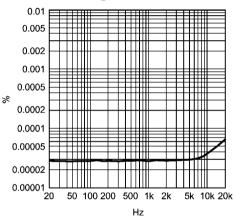
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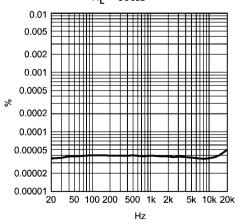
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# THD+N vs Frequency $\begin{aligned} V_{CC} &= 22V, \, V_{EE} = -22V, \, V_{OUT} = 3V_{RMS} \\ R_L &= 2k\Omega \end{aligned}$



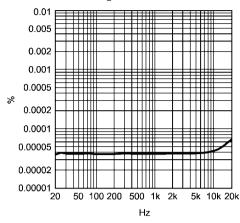
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THD+N vs Frequency 
$$\begin{aligned} V_{CC} = 12V, \, V_{EE} = -12V, \, V_{OUT} = 3V_{RMS} \\ R_L = 600\Omega \end{aligned}$$



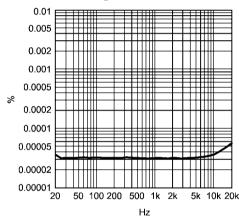
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$$\begin{aligned} & \text{THD+N vs Frequency} \\ V_{CC} &= 12V, \, V_{EE} = -12V, \, V_{OUT} = 3V_{RMS} \\ & R_1 = 2k\Omega \end{aligned}$$



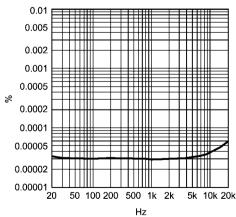
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# THD+N vs Frequency $\begin{aligned} V_{CC} = 15V, \, V_{EE} = -15V, \, V_{OUT} = 3V_{RMS} \\ R_L = 600\Omega \end{aligned}$

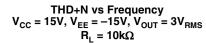


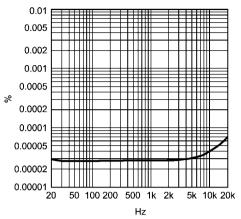
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THD+N vs Frequency 
$$\begin{aligned} &V_{CC} = 22V, \, V_{EE} = -22V, \, V_{OUT} = 3V_{RMS} \\ &R_L = 600\Omega \end{aligned}$$



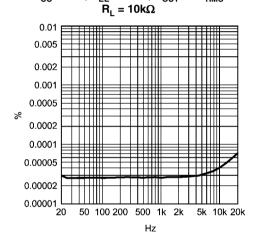
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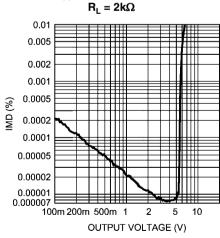
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# THD+N vs Frequency V<sub>CC</sub> = 22V, V<sub>EE</sub> = -22V, V<sub>OUT</sub> = 3V<sub>RMS</sub>

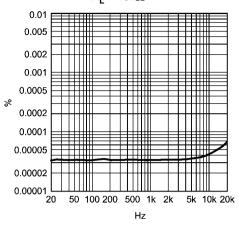


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## IMD vs Output Voltage $V_{CC} = 12V$ , $V_{EE} = -12V$

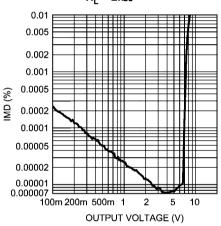


THD+N vs Frequency 
$$\begin{split} V_{CC} &= 12V, \, V_{EE} = -12V, \, V_{OUT} = 3V_{RMS} \\ R_I &= 10k\Omega \end{split}$$



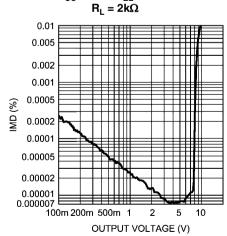
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IMD vs Output Voltage  $V_{CC}$  = 15V,  $V_{EE}$  = -15V  $R_L$  = 2k $\Omega$ 



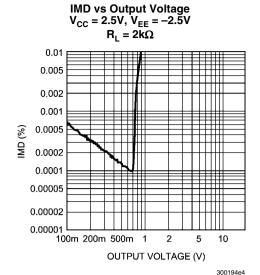
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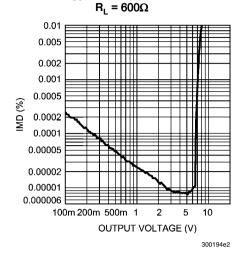
IMD vs Output Voltage 
$$V_{CC} = 22V$$
,  $V_{EE} = -22V$ 



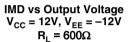
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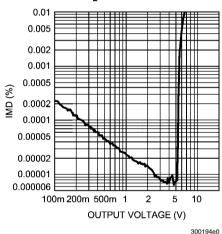
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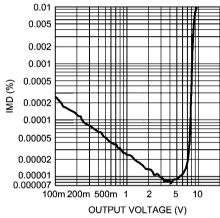


IMD vs Output Voltage  $V_{CC} = 15V$ ,  $V_{EE} = -15V$ 





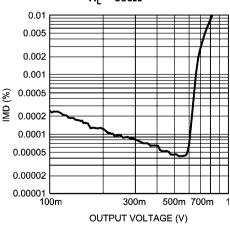
IMD vs Output Voltage  $V_{CC}$  = 22V,  $V_{EE}$  = -22V  $R_L$  =  $600\Omega$ 



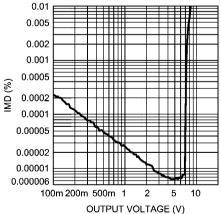
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IMD vs Output Voltage  $V_{CC}$  = 2.5V,  $V_{EE}$  = -2.5V  $R_{L}$  = 600 $\Omega$ 

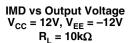


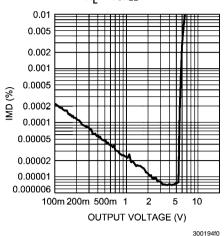
IMD vs Output Voltage  $V_{CC} = 15V$ ,  $V_{EE} = -15V$   $R_L = 10k\Omega$ 



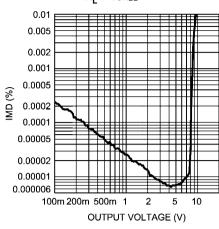
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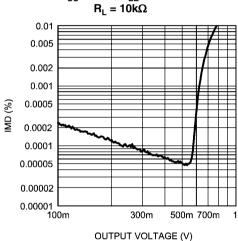


# IMD vs Output Voltage $V_{CC}$ = 22V, $V_{EE}$ = -22V $R_{L}$ = 10k $\Omega$

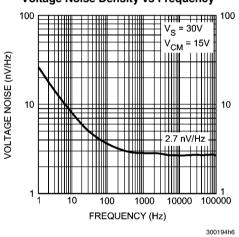


300194f2

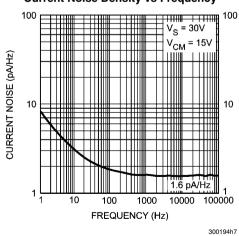
## IMD vs Output Voltage $V_{CC} = 2.5V$ , $V_{EE} = -2.5V$



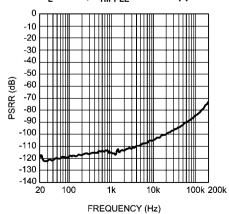
### Voltage Noise Density vs Frequency



**Current Noise Density vs Frequency** 

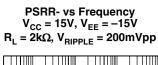


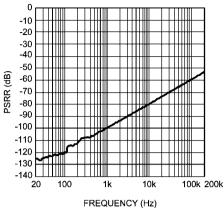
 $\begin{aligned} & PSRR+ \ vs \ Frequency \\ & V_{CC} = 15V, \ V_{EE} = -15V \\ & R_L = 2k\Omega, \ V_{RIPPLE} = 200mVpp \end{aligned}$ 



300194p7

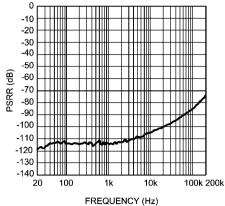
30019416





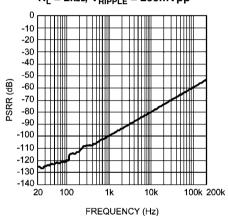
300194r2

# PSRR+ vs Frequency $V_{CC}$ = 17V, $V_{EE}$ = -17V $R_L$ = 2k $\Omega$ , $V_{RIPPLE}$ = 200mVpp



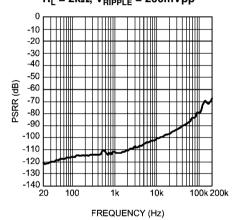
300194a0

### **PSRR- vs Frequency** V<sub>CC</sub> = 17V, V<sub>EE</sub> = -17V $R_L = 2k\Omega$ , $V_{RIPPLE} = 200mVpp$



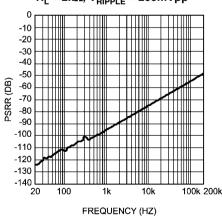
300194r2

**PSRR+ vs Frequency**  $V_{CC} = 12V, V_{EE} = -12V$  $R_L = 2k\Omega$ ,  $V_{RIPPLE} = 200mVpp$ 



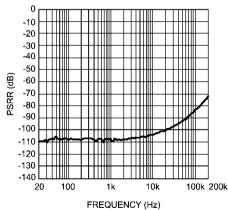
300194p4

### **PSRR- vs Frequency** $V_{CC} = 12V, V_{EE} = -12V$ $R_L = 2k\Omega$ , $V_{RIPPLE} = 200mVpp$

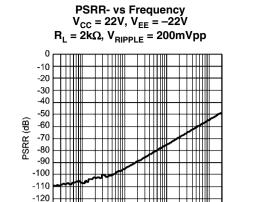


300194q9

### **PSRR+ vs Frequency** $V_{CC} = 22V, V_{EE} = -22V$ $R_L = 2k\Omega$ , $V_{RIPPLE} = 200mVpp$



300194q3



-130

-140

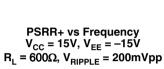
20

100

10k FREQUENCY (Hz)

300194r8

100k 200k



-20

-30

-40

-50

-70

-80

-90

-100

-110

-120

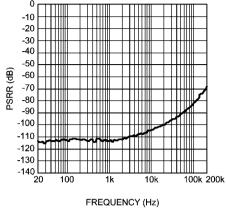
-130

-140

20

100

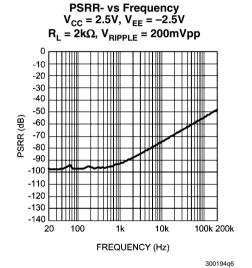
PSRR (dB) -60



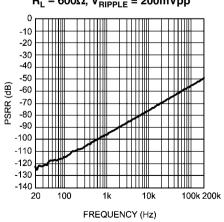
 $\begin{aligned} & \text{PSRR+ vs Frequency} \\ & \text{V}_{\text{CC}} = 2.5\text{V}, \, \text{V}_{\text{EE}} = -2.5\text{V} \\ & \text{R}_{\text{L}} = 2\text{k}\Omega, \, \text{V}_{\text{RIPPLE}} = 200\text{mVpp} \end{aligned}$ 

300194p1

100k 200k

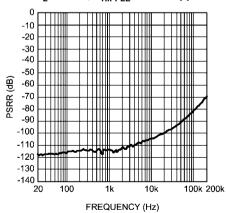


PSRR- vs Frequency  $V_{CC} = 15V$ ,  $V_{EE} = -15V$  $R_L = 600\Omega$ ,  $V_{RIPPLE} = 200 \text{mVpp}$ 



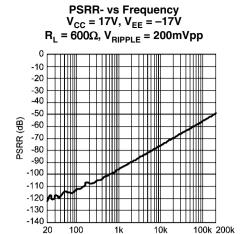
300194p9 PSRR+ vs Frequency  $V_{CC} = 17V$ ,  $V_{EE} = -17V$  $R_L = 600\Omega$ ,  $V_{RIPPLE} = 200 \text{mVpp}$ 

1k FREQUENCY (Hz)

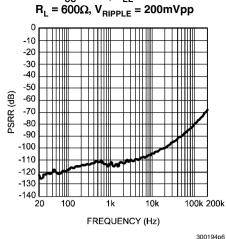


300194q2

300194r4



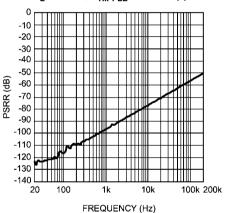
300194r7



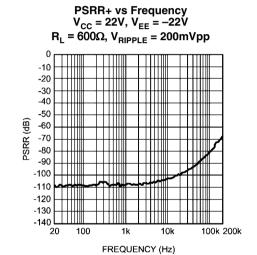
PSRR+ vs Frequency V<sub>CC</sub> = 12V, V<sub>EE</sub> = -12V



FREQUENCY (Hz)

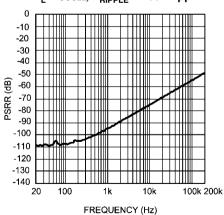


300194r1

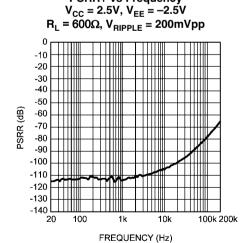


300194q5

## **PSRR- vs Frequency** $V_{CC}$ = 22V, $V_{EE}$ = -22V $R_L$ = 600 $\Omega$ , $V_{RIPPLE}$ = 200mVpp

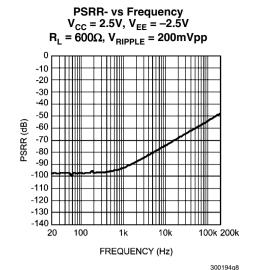


300194s0

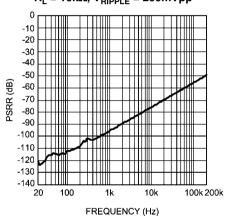


**PSRR+ vs Frequency** 

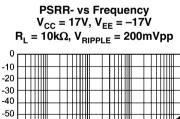
300194p3

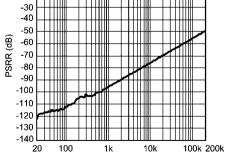


 $\begin{aligned} & \text{PSRR- vs Frequency} \\ & \text{V}_{\text{CC}} = 15\text{V}, \, \text{V}_{\text{EE}} = -15\text{V} \\ & \text{R}_{\text{L}} = 10\text{k}\Omega, \, \text{V}_{\text{RIPPLE}} = 200\text{mVpp} \end{aligned}$ 



300194r3

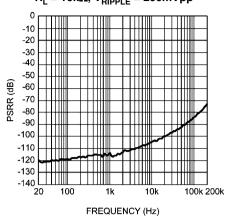




FREQUENCY (Hz)

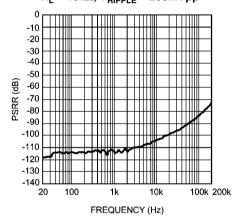
300194r6

PSRR+ vs Frequency  $V_{CC} = 15V, \, V_{EE} = -15V \\ R_L = 10k\Omega, \, V_{RIPPLE} = 200mVpp \label{eq:RL}$ 



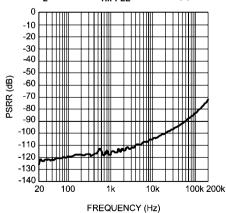
300194p8

 $\begin{array}{c} \text{PSRR+ vs Frequency} \\ \text{V}_{\text{CC}} = 17\text{V}, \, \text{V}_{\text{EE}} = -17\text{V} \\ \text{R}_{L} = 10\text{k}\Omega, \, \text{V}_{\text{RIPPLE}} = 200\text{mVpp} \end{array}$ 

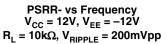


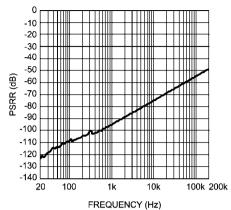
300194q1

 $\begin{array}{c} \text{PSRR+ vs Frequency} \\ \text{V}_{\text{CC}} = 12\text{V}, \, \text{V}_{\text{EE}} = -12\text{V} \\ \text{R}_{\text{L}} = 10\text{k}\Omega, \, \text{V}_{\text{RIPPLE}} = 200\text{mVpp} \end{array}$ 



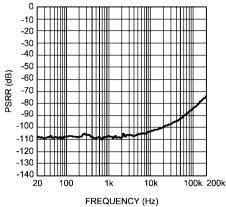
300194p5





300194r0

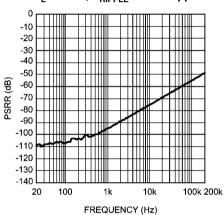
# PSRR+ vs Frequency $V_{CC}$ = 22V, $V_{EE}$ = -22V $R_L$ = 10k $\Omega$ , $V_{RIPPLE}$ = 200mVpp



300194q4

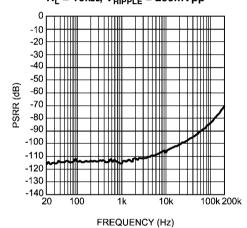
### PSRR- vs Frequency V<sub>CC</sub> = 22V, V<sub>EE</sub> = -22V





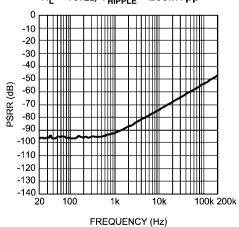
300194r9

# $$\begin{split} & \text{PSRR+ vs Frequency} \\ & \text{V}_{\text{CC}} = 2.5\text{V}, \, \text{V}_{\text{EE}} = -2.5\text{V} \\ & \text{R}_{\text{L}} = 10\text{k}\Omega, \, \text{V}_{\text{RIPPLE}} = 200\text{mVpp} \end{split}$$



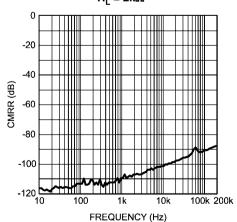
300194p2

# $\begin{aligned} & \text{PSRR- vs Frequency} \\ & \text{V}_{\text{CC}} = 2.5\text{V}, \, \text{V}_{\text{EE}} = -2.5\text{V} \\ & \text{R}_{\text{L}} = 10\text{k}\Omega, \, \text{V}_{\text{RIPPLE}} = 200\text{mVpp} \end{aligned}$

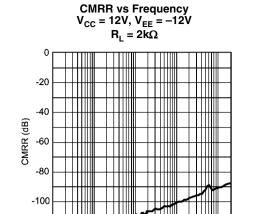


300194q7

# CMRR vs Frequency $V_{CC}$ = 15V, $V_{EE}$ = -15V $R_L$ = $2k\Omega$

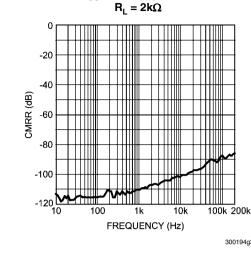


300194q0



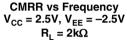
300194f7

100k 200k



CMRR vs Frequency V<sub>CC</sub> = 22V, V<sub>EE</sub> = -22V

300194g3



FREQUENCY (Hz)

-120 l 10

0

-20

-40

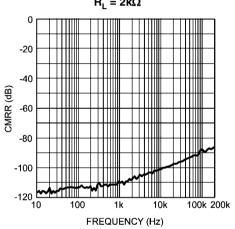
-60

-80

-100

-120 E 10

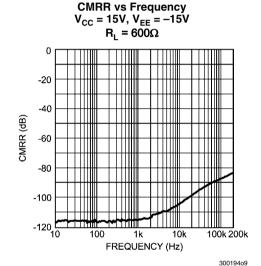
CMRR (dB)



CMRR vs Frequency  $V_{CC}$  = 12V,  $V_{EE}$  = -12V  $R_L$  = 600 $\Omega$ 

FREQUENCY (Hz)

300194f4

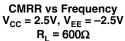


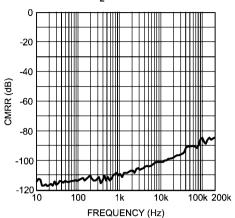
CMRR vs Frequency  $V_{CC}$  = 22V,  $V_{EE}$  = -22V  $R_L$  = 600 $\Omega$ 



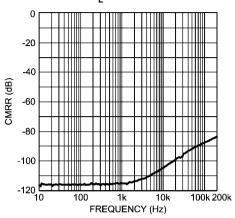
-20 -40 CMRR (dB) -60 -80 -100 -120 10 100 100k 200k 1k FREQUENCY (Hz)

300194g5





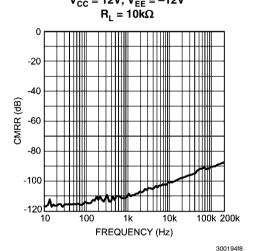
CMRR vs Frequency  $V_{CC}$  = 15V,  $V_{EE}$  = -15V  $R_L$  = 10k $\Omega$ 



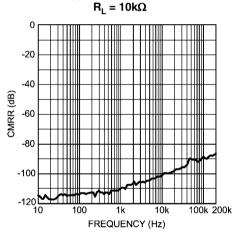
30019408

## CMRR vs Frequency V<sub>CC</sub> = 12V, V<sub>EE</sub> = -12V

300194f6

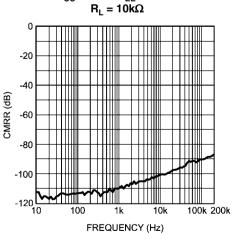


CMRR vs Frequency V<sub>CC</sub> = 22V, V<sub>EE</sub> = -22V

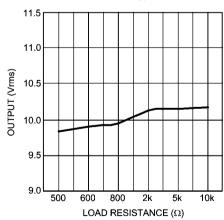


300194g4

# CMRR vs Frequency $V_{CC}$ = 2.5V, $V_{EE}$ = -2.5V $R_{L}$ = 10k $\Omega$



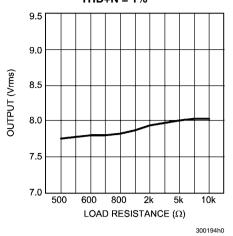
Output Voltage vs Load Resistance  $V_{CC}$  = 15V,  $V_{EE}$  = -15V THD+N = 1%



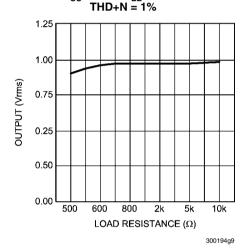
300194h1

300194f5

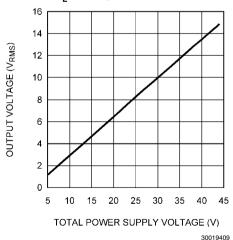
# Output Voltage vs Load Resistance $V_{CC}$ = 12V, $V_{EE}$ = -12V THD+N = 1%



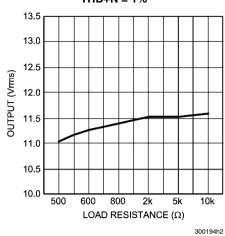
## Output Voltage vs Load Resistance $V_{CC} = 2.5V$ , $V_{EE} = -2.5V$



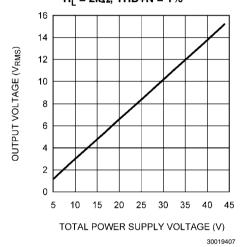
## Output Voltage vs Total Power Supply Voltage $R_1 = 600\Omega$ , THD+N = 1%



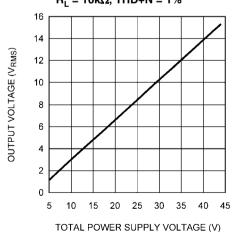
# Output Voltage vs Load Resistance $V_{CC}$ = 22V, $V_{EE}$ = -22V THD+N = 1%



## Output Voltage vs Total Power Supply Voltage $R_1 = 2k\Omega$ , THD+N = 1%

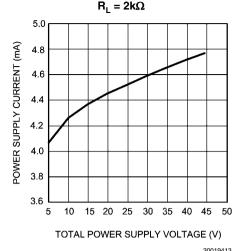


## Output Voltage vs Total Power Supply Voltage $R_{_{L}}=10k\Omega,\,THD+N=1\%$

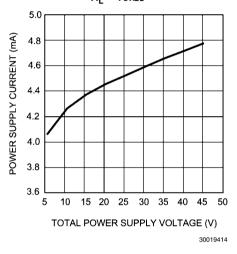


30019408

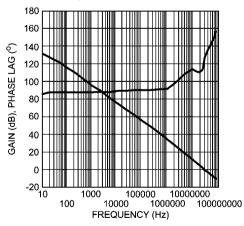
## **Power Supply Current vs Total Power Supply Voltage**



### **Power Supply Current vs Total Power Supply Voltage** $R_L = 10k\Omega$

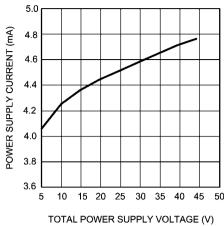


#### Gain Phase vs Frequency $V_s = \pm 18V, R_1 = 2k\Omega$

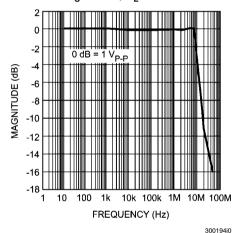


300194j1

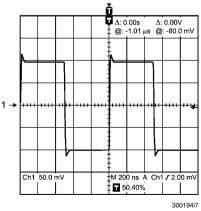
#### **Power Supply Current vs Total Power Supply Voltage** $R_1 = 600\Omega$



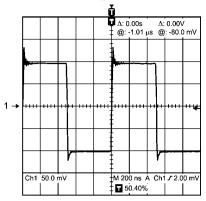
#### **Full Power Bandwidth vs Frequency** $V_S = \pm 18V$ , $R_L = 2k\Omega$



#### **Small-Signal Transient Response** $A_{V} = 1, C_{L} = 10pF$



## Small-Signal Transient Response $A_V = 1$ , $C_L = 100 pF$



300194i8

### **Application Information**

#### **DISTORTION MEASUREMENTS**

The vanishingly low residual distortion produced by LME49870 is below the capabilities of all commercially available equipment. This makes distortion measurements just slightly more difficult than simply connecting a distortion meter to the amplifier's inputs and outputs. The solution, however, is quite simple: an additional resistor. Adding this resistor extends the resolution of the distortion measurement equipment.

The LME49870's low residual distortion is an input referred internal error. As shown in Figure 1, adding the  $10\Omega$  resistor connected between the amplifier's inverting and non-inverting

inputs changes the amplifier's noise gain. The result is that the error signal (distortion) is amplified by a factor of 101. Although the amplifier's closed-loop gain is unaltered, the feedback available to correct distortion errors is reduced by 101, which means that measurement resolution increases by 101. To ensure minimum effects on distortion measurements, keep the value of R1 low as shown in Figure 1.

This technique is verified by duplicating the measurements with high closed loop gain and/or making the measurements at high frequencies. Doing so produces distortion components that are within the measurement equipment's capabilities. This datasheet's THD+N and IMD values were generated using the above described circuit connected to an Audio Precision System Two Cascade.

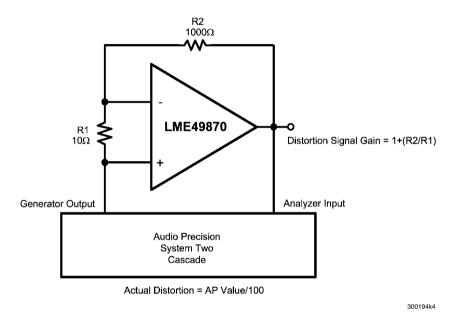
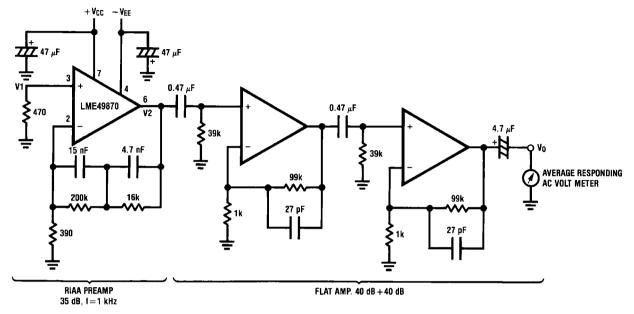


FIGURE 1. THD+N and IMD Distortion Test Circuit

The LME49870 is a high speed op amp with excellent phase margin and stability. Capacitive loads up to 100pF will cause little change in the phase characteristics of the amplifiers and are therefore allowable.

Capacitive loads greater than 100pF must be isolated from the output. The most straightforward way to do this is to put a resistor in series with the output. This resistor will also prevent excess power dissipation if the output is accidentally shorted.

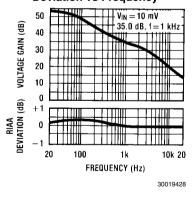


30019427

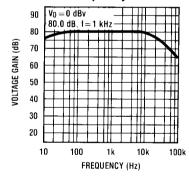
Complete shielding is required to prevent induced pick up from external sources. Always check with oscilloscope for power line noise.

Noise Measurement Circuit Total Gain: 115 dB @f = 1 kHz Input Referred Noise Voltage:  $e_n = V0/560,000$  (V)

## RIAA Preamp Voltage Gain, RIAA Deviation vs Frequency

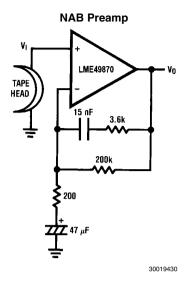


#### Flat Amp Voltage Gain vs Frequency

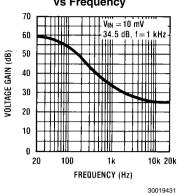


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### **TYPICAL APPLICATIONS**

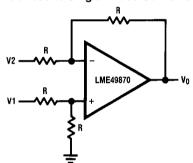


NAB Preamp Voltage Gain vs Frequency



 $A_V = 34.5$ . F = 1 kHz  $E_n = 0.38 \; \mu V$ A Weighted

**Balanced to Single Ended Converter** 

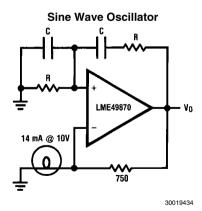


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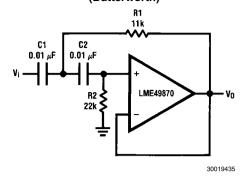
 $V_0 = V1 - V2$ 

LME49870 30019433  $V_0 = V1 + V2 - V3 - V4$ 

Adder/Subtracter



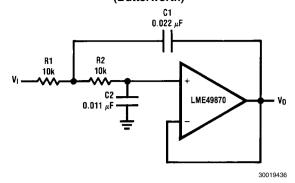
## Second Order High Pass Filter (Butterworth)



$$R1 = \frac{\sqrt{2}}{2\omega_{\rm p}C}$$

Illustration is  $f_0 = 1 \text{ kHz}$ 

## Second Order Low Pass Filter (Butterworth)

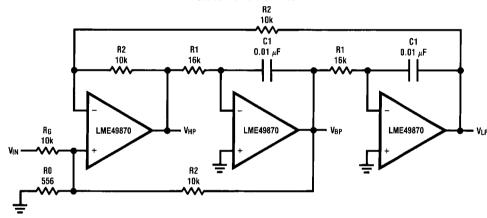


$$C1 = \frac{\sqrt{2}}{m \cdot R}$$

$$C2 = \frac{C1}{2}$$

Illustration is f<sub>0</sub> = 1 kHz

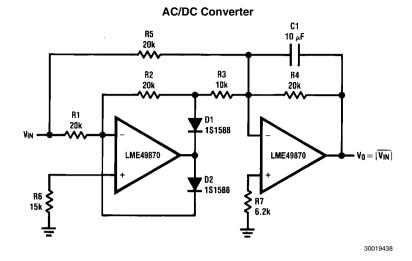
### State Variable Filter



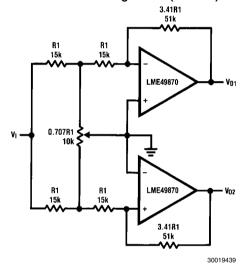
30019437

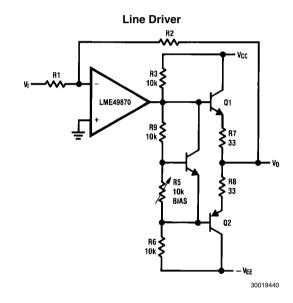
$$f_0 = \frac{1}{2\pi C1R1}, Q = \frac{1}{2}\left(1 + \frac{R2}{R0} + \frac{R2}{RG}\right), A_{BP} = QA_{LP} = QA_{LH} = \frac{R2}{RG}$$

Illustration is  $f_0 = 1 \text{ kHz}$ , Q = 10,  $A_{BP} = 1$ 

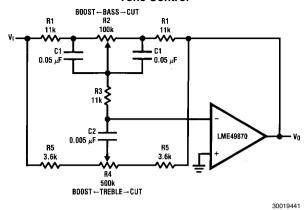


### 2 Channel Panning Circuit (Pan Pot)





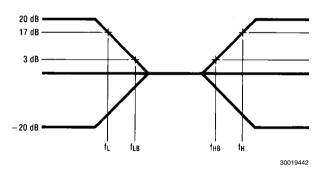
#### **Tone Control**



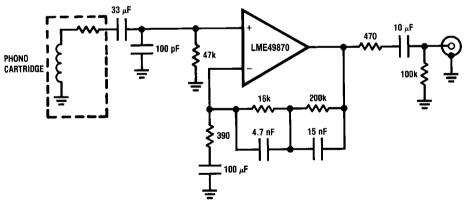
$$\begin{split} f_L &= \frac{1}{2\pi R2C1}, f_{LB} = \frac{1}{2\pi R1C1} \\ f_H &= \frac{1}{2\pi R5C2}, f_{HB} = \frac{1}{2\pi (R1 + R5 + 2R3)C2} \end{split}$$

Illustration is:

$$f_L = 32 \text{ Hz}, f_{LB} = 320 \text{ Hz}$$
  
 $f_H = 11 \text{ kHz}, f_{HB} = 1.1 \text{ kHz}$ 

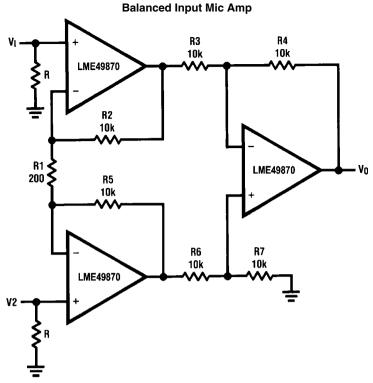


#### **RIAA Preamp**



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 $\begin{array}{l} A_{\nu}=35~dB\\ E_{n}=0.33~\mu V\\ S/N=90~dB\\ f=1~kHz\\ A~Weighted\\ A~Weighted,~V_{IN}=10~mV\\ @~f=1~kHz\\ \end{array}$ 



30019443

If R2 = R5, R3 = R6, R4 = R7  

$$V0 = \left(1 + \frac{2R2}{R1}\right) \frac{R4}{R3} (V2 - V1)$$

Illustration is: V0 = 101(V2 - V1)

## 

30019444

fo (Hz)	C <sub>1</sub>	$C_2$	R <sub>1</sub>	R <sub>2</sub>
32	0.12µF	4.7µF	75kΩ	500Ω
64	0.056µF	3.3µF	68kΩ	510Ω
125	0.033µF	1.5µF	62kΩ	510Ω
250	0.015µF	0.82µF	68kΩ	470Ω
500	8200pF	0.39µF	62kΩ	470Ω
1k	3900pF	0.22µF	68kΩ	470Ω
2k	2000pF	0.1µF	68kΩ	470Ω
4k	1100pF	0.056µF	62kΩ	470Ω
8k	510pF	0.022µF	68kΩ	510Ω
16k	330pF	0.012µF	51kΩ	510Ω

**Note 9:** At volume of change =  $\pm 12 \text{ dB}$ 

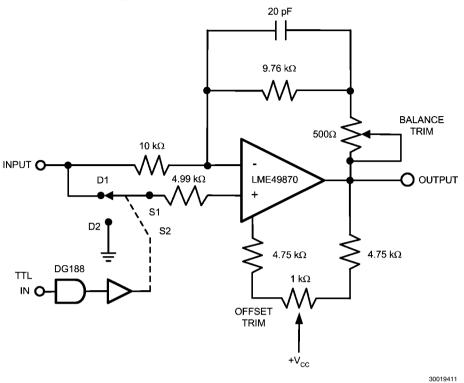
Q = 1.7

Reference: "AUDIO/RADIO HANDBOOK", National Semiconductor, 1980, Page 2-61

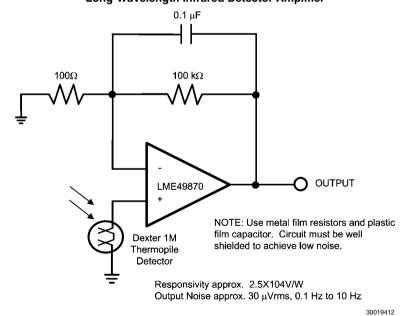
# **Headphone Amplifier** +15V $0.1~\mu F$ $1 \, k\Omega$ INPUT O LME49870 200Ω This application uses two op amps in parallel for higher current То 200Ω Headphone drive. LME49870 -15V

30019410

#### **High Performance Synchronous Demodulator**



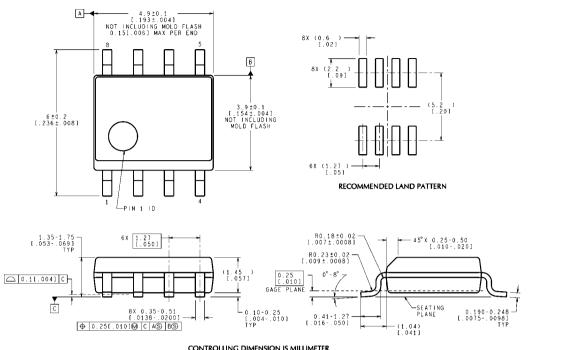
### **Long-Wavelength Infrared Detector Amplifier**



## **Revision History**

Rev	Date	Description
1.0	09/20/07	Initial release.
1.1	09/27/07	Updated Notes 1–7 (per National standard).
1.2	12/20/07	Deleted all Crosstalk vs Frequency curves.
1.3	01/14/08	Edited some graphics.

## Physical Dimensions inches (millimeters) unless otherwise noted



CONTROLLING DIMENSION IS MILLIMETER
VALUES IN [ ] ARE INCHES
DIMENSIONS IN ( ) FOR REFERENCE ONLY

M08A (Rev L)

Narrow SOIC Package Order Number LME49870MA NS Package Number M08A

Notes	LME49870
	0

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Clock Conditioners	www.national.com/timing	App Notes	www.national.com/appnotes	
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